

# P-Channel 12 V (D-S) MOSFET

MOSFET PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) Max.	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)
- 12	0.028 at V <sub>GS</sub> = - 4.5 V	- 6 <sup>e</sup>	9 nC
	0.032 at V <sub>GS</sub> = - 3.7 V	- 6 <sup>e</sup>	
	0.040 at V <sub>GS</sub> = - 2.5 V	- 6 <sup>e</sup>	
	0.063 at V <sub>GS</sub> = - 1.8 V	- 4.5	
	0.150 at V <sub>GS</sub> = - 1.5 V	- 3.6	

## FEATURES

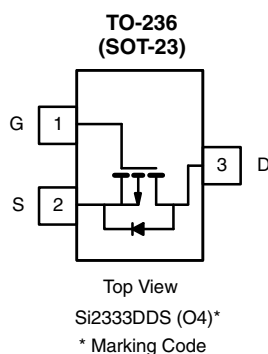
- TrenchFET® Power MOSFET
- 100 % R<sub>g</sub> Tested
- Material categorization:  
For definitions of compliance please see  
[www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

## APPLICATIONS

- Smart Phones and Tablet PCs
- Load Switch
- Battery Switch



Ordering Information: Si2333DDS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V <sub>DS</sub>	- 12	V
Gate-Source Voltage		V <sub>GS</sub>	± 8	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 25 °C	I <sub>D</sub>	- 6 <sup>e</sup>	A
	T <sub>C</sub> = 70 °C		- 5.2	
	T <sub>A</sub> = 25 °C		- 5 <sup>b, c</sup>	
	T <sub>A</sub> = 70 °C		- 4 <sup>b, c</sup>	
Pulsed Drain Current (t = 300 μs)		I <sub>DM</sub>	- 20	
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C	I <sub>S</sub>	- 1.4	A
	T <sub>A</sub> = 25 °C		- 0.63 <sup>b, c</sup>	
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	1.7	W
	T <sub>C</sub> = 70 °C		1.1	
	T <sub>A</sub> = 25 °C		1.20 <sup>b, c</sup>	
	T <sub>A</sub> = 70 °C		0.6 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b, d</sup>	≤ 5 s	R <sub>thJA</sub>	100	130	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	60	75	

Notes:

- Based on T<sub>C</sub> = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 5 s.
- Maximum under steady state conditions is 175 °C/W.
- Package limited.

MOSFET SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>DS</sub> = 0 V, I <sub>D</sub> = - 250 μA	- 12			V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = - 250 μA		- 8		mV/°C
V <sub>GS(th)</sub> Temperature Coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>			2.4		
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = - 250 μA	- 0.4		- 1	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 8 V			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 12 V, V <sub>GS</sub> = 0 V			- 1	μA
		V <sub>DS</sub> = - 12 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			- 10	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≤ - 5 V, V <sub>GS</sub> = - 4.5 V	- 20			A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 5 A		0.023	0.028	Ω
		V <sub>GS</sub> = - 3.7 V, I <sub>D</sub> = - 4.6 A		0.026	0.032	
		V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 4.3 A		0.033	0.040	
		V <sub>GS</sub> = - 1.8 V, I <sub>D</sub> = - 1 A		0.048	0.063	
		V <sub>GS</sub> = - 1.5 V, I <sub>D</sub> = - 0.5 A		0.075	0.150	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = - 5 V, I <sub>D</sub> = - 5 A		18		S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = - 6 V, V <sub>GS</sub> = 0 V, f = 1 MHz		1275		pF
Output Capacitance	C <sub>oss</sub>			255		
Reverse Transfer Capacitance	C <sub>rss</sub>			236		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = - 6 V, V <sub>GS</sub> = - 8 V, I <sub>D</sub> = - 5 A		23	35	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> = - 6 V, V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 5 A		14	21	
Gate-Drain Charge	Q <sub>gd</sub>			2.3		
Gate Resistance	R <sub>g</sub>			3.6		
Gate Resistance	R <sub>g</sub>	f = 1 MHz	1.9	9.5	19	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = - 6 V, R <sub>L</sub> = 6 Ω I <sub>D</sub> = - 4 A, V <sub>GEN</sub> = - 4.5 V, R <sub>G</sub> = 1 Ω		26	40	ns
Rise Time	t <sub>r</sub>			24	40	
Turn-Off Delay Time	t <sub>d(off)</sub>			45	70	
Fall Time	t <sub>f</sub>			20	35	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			- 1.4	A
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>				- 20	
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = - 4 A		- 0.8	- 1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 4 A, dI/dt = 100 A/μs, T <sub>J</sub> = 25 °C		24	48	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			8	16	nC
Reverse Recovery Fall Time	t <sub>a</sub>			9		ns
Reverse Recovery Rise Time	t <sub>b</sub>			15		

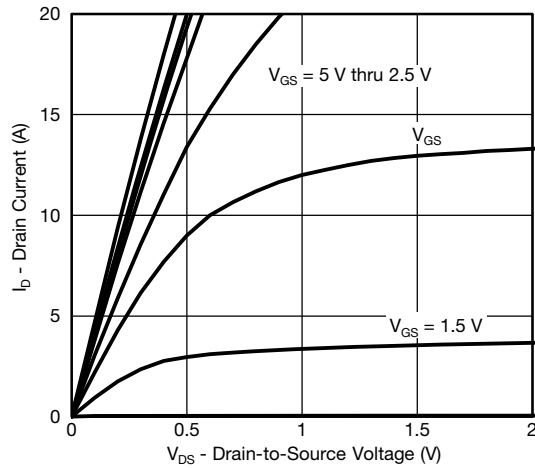
Notes:

a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

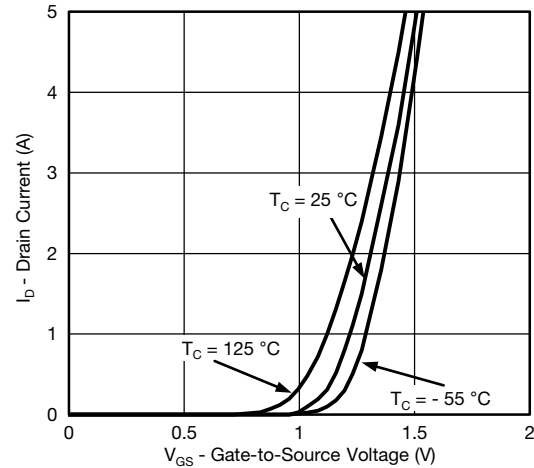
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

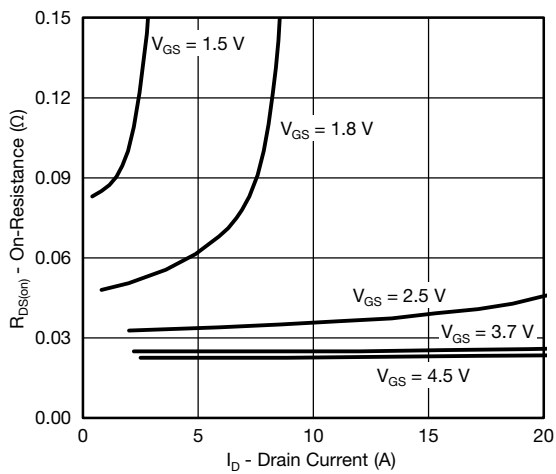
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



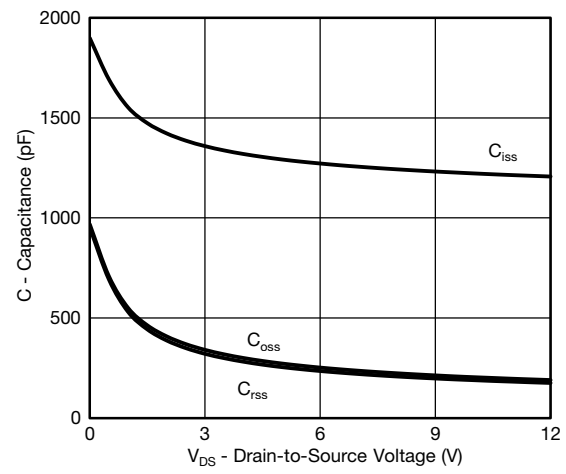
Output Characteristics



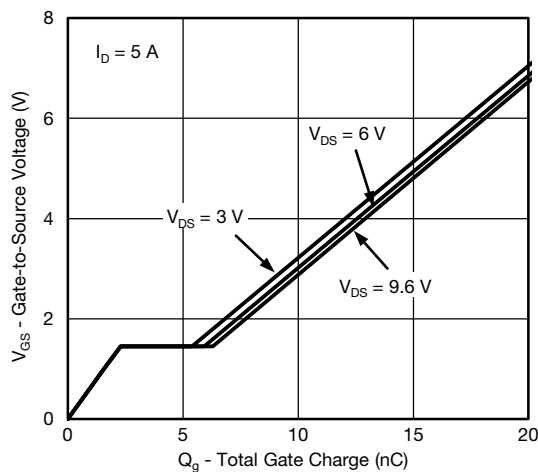
Transfer Characteristics



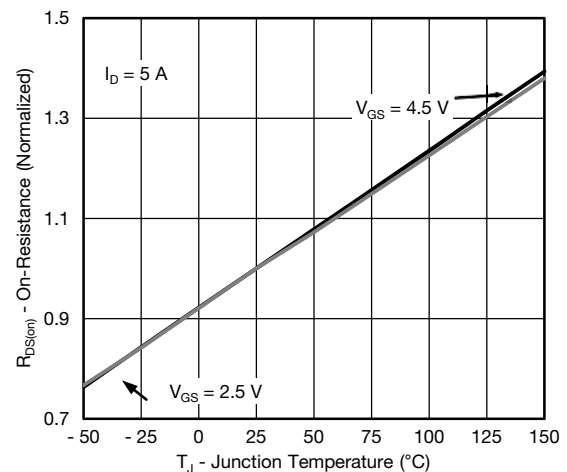
On-Resistance vs. Drain Current and Gate Voltage



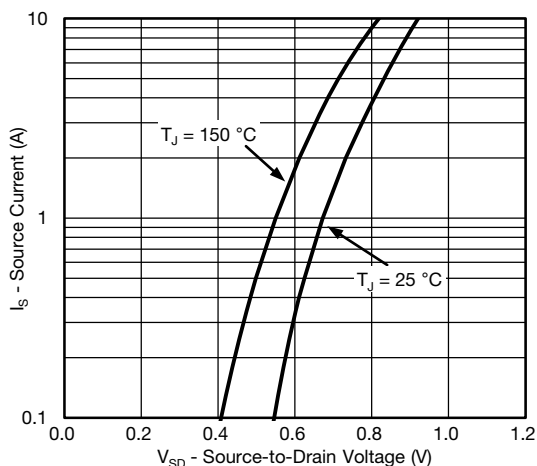
Capacitance



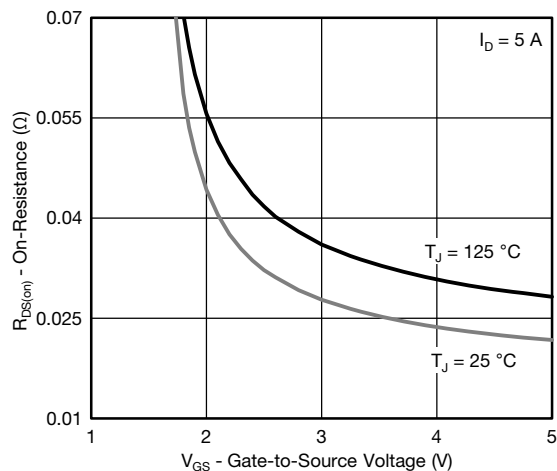
Gate Charge



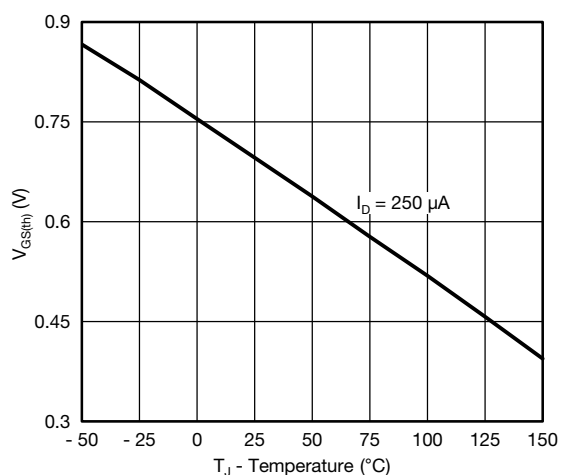
On-Resistance vs. Junction Temperature

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

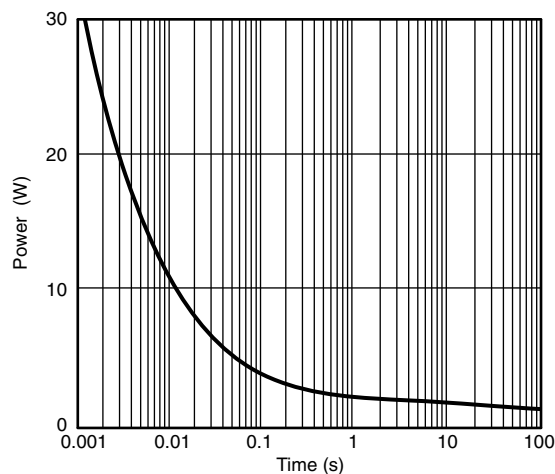
Source-Drain Diode Forward Voltage



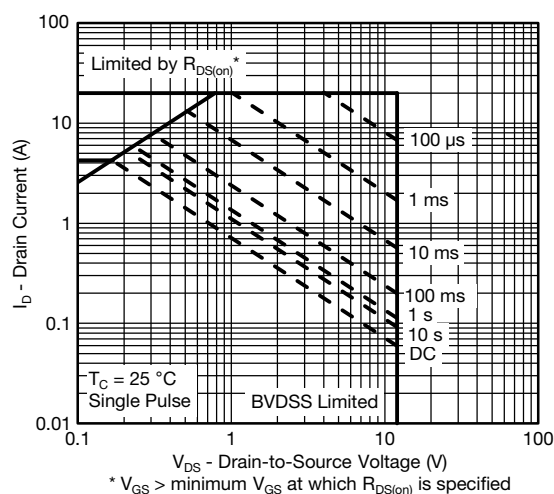
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

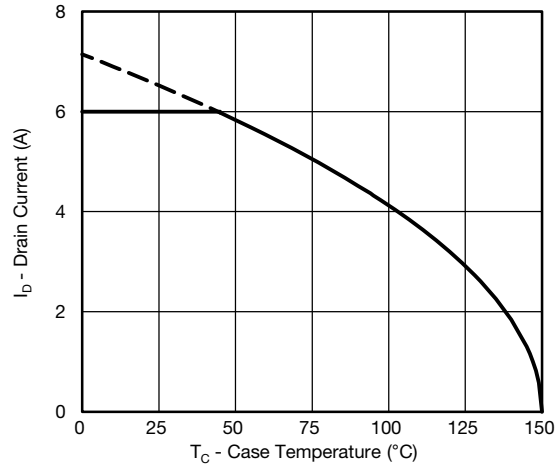


Single Pulse Power

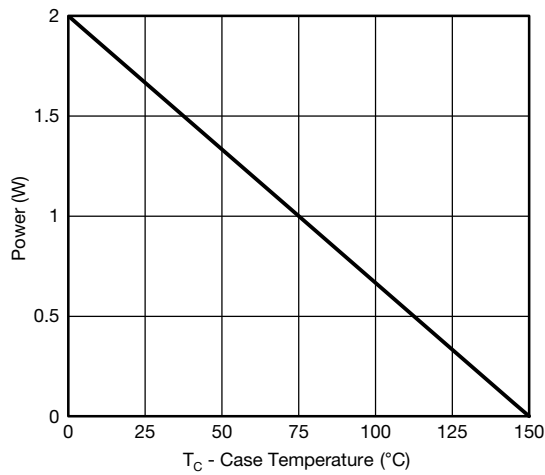


Safe Operating Area

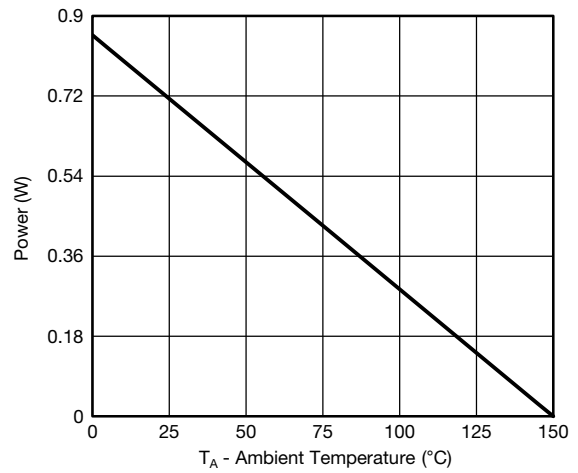
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating\*

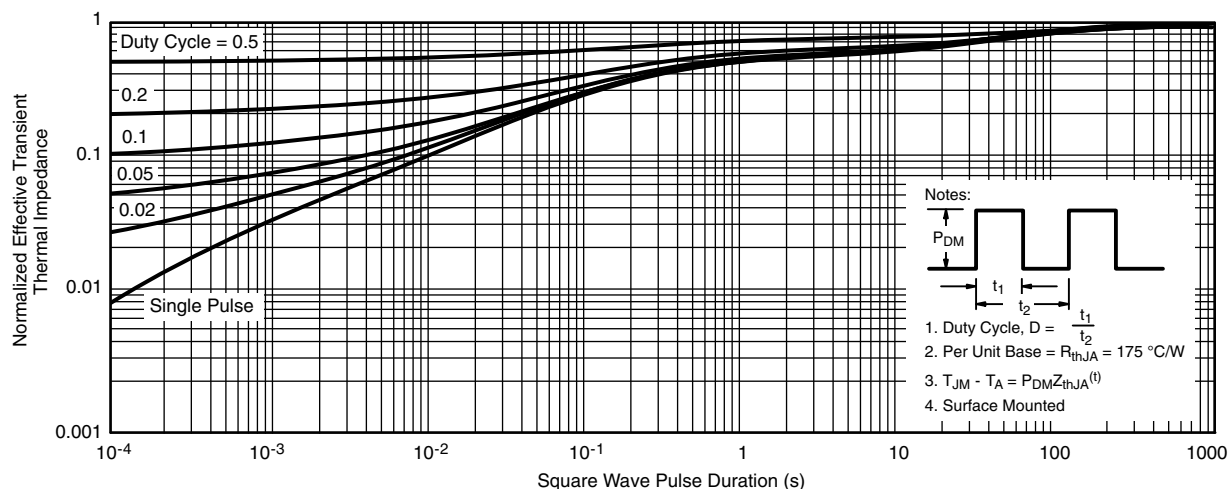
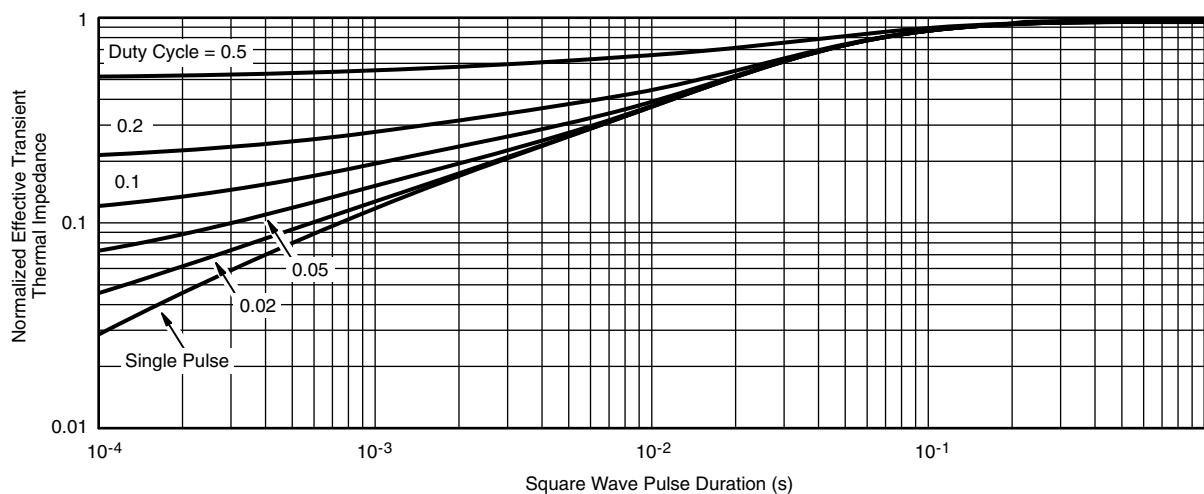


Power, Junction-to-Case



Power, Junction-to-Ambient

\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150\text{ °C}$ , using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Foot**

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## SOT-23 (TO-236): 3-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A <sub>1</sub>	0.01	0.10	0.0004	0.004
A <sub>2</sub>	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E <sub>1</sub>	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e <sub>1</sub>	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L <sub>1</sub>	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°
ECN: S-03946-Rev. K, 09-Jul-01 DWG: 5479				

## RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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